# NSN 5961-01-514-2180

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# Inclosure Material:

Metal

**Overall Length:** 

0.975 inches

# **Overall Height:**

0.200 inches

**Overall Width:** 

0.670 inches

# Mounting Facility Quantity:

2

# **Mounting Method:**

Slot

#### **Features Provided:**

Low noise

#### Semiconductor Material:

Silicon

### Voltage Rating In Volts Per Characteristic:

70.0 drain to gate voltage and 70.0 drain to source voltage and 30.0 gate to source voltage

## **Current Rating Per Characteristic:**

4.00 amperes source cutoff current of standard range

## Power Rating Per Characteristic:

100.0 watts small-signal input power, common-collector absolute

#### **Product Name:**

Silicon rf power, vdmos transistor

## **Special Features:**

8gold metalized; package style - ak; high efficiency; linear; high gain; junction temperature plus 200.0 degrees c; storage temperature minus 65.0 to plus 150.0 degrees c; designed specifically for broadband radio frequency (rf) applications

## Terminal Type And Quantity:

2 tab, solder lug

Shelf Life:

N/a

#### Unit Of Measure:

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#### Demilitarization:

No

Fiig:

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